



## Description

The FDD6635 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = 40V$   $I_D = 60A$

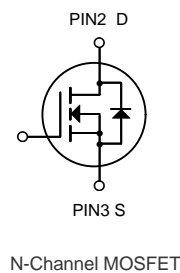
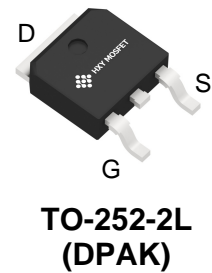
$R_{DS(ON)} < 8.5m\Omega$  @  $V_{GS}=10V$

## Application

Battery protection

Load switch

Uninterruptible power supply



## Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
FDD6635	TO-252-2L(DPAK)	HXY MOSFET	2500

## Absolute Maximum Ratings ( $T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	60	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	45	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	220	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	416.1	mJ
$I_{AS}$	Avalanche Current	39	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation <sup>4</sup>	64.6	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^{\circ}C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	62	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	2.8	$^{\circ}C/W$



### Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	40	45	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.2	1.6	2.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	7.0	8.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		15	18	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =20A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, F=1.0MHz	-	1800	-	PF
Output Capacitance	C <sub>OSS</sub>		-	280	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	190	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V, I <sub>D</sub> =2A, R <sub>L</sub> =1Ω V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	6.4	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	17.2	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	29.6	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	16.8	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	29		nC
Gate-Source Charge	Q <sub>gs</sub>		-	4.5		nC
Gate-Drain Charge	Q <sub>gd</sub>		-	6.4		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =10A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	68	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A di/dt = 100A/μs(Note3)	-	29	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	26	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E<sub>AS</sub> condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=20V, V<sub>G</sub>=10V, L=1mH, R<sub>G</sub>=25Ω,



### Typical Electrical and Thermal Characteristics (Curves)

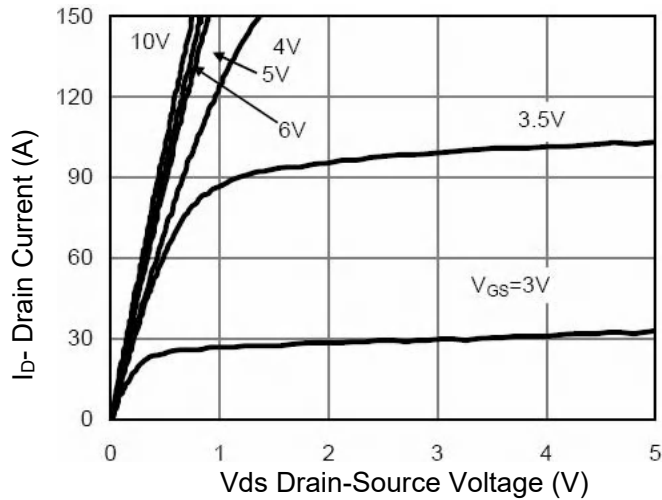


Figure 1 Output Characteristics

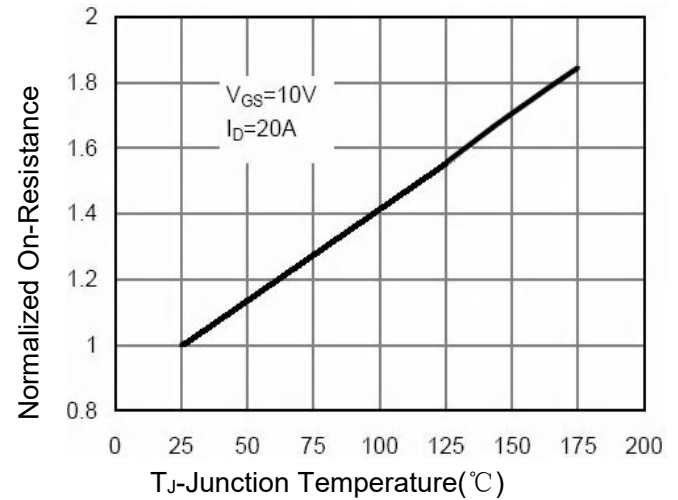


Figure 4 Rdson-Junction Temperature

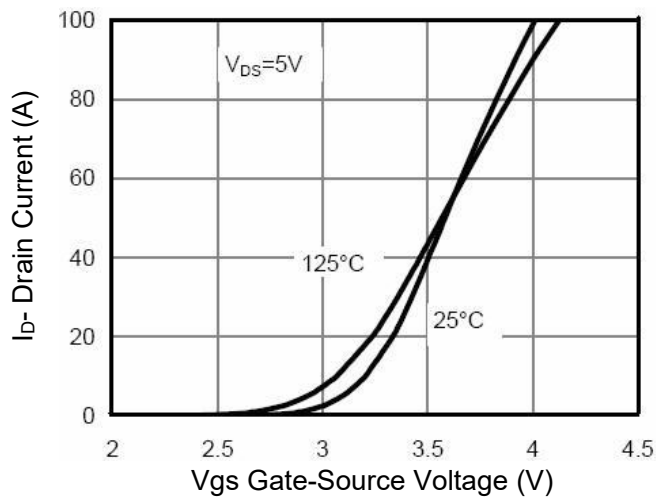


Figure 2 Transfer Characteristics

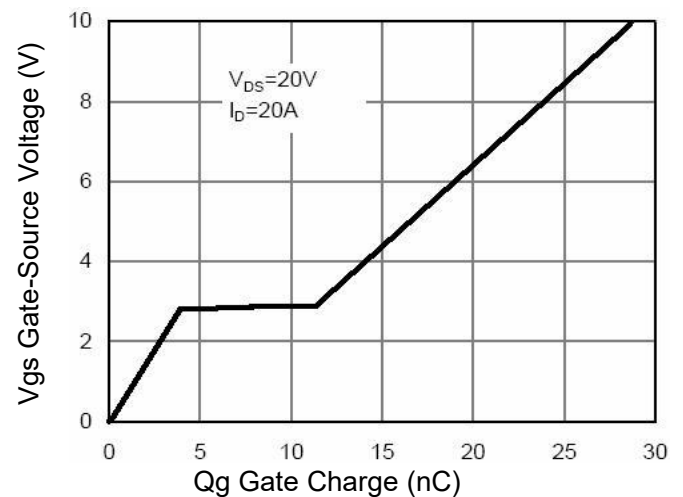


Figure 5 Gate Charge

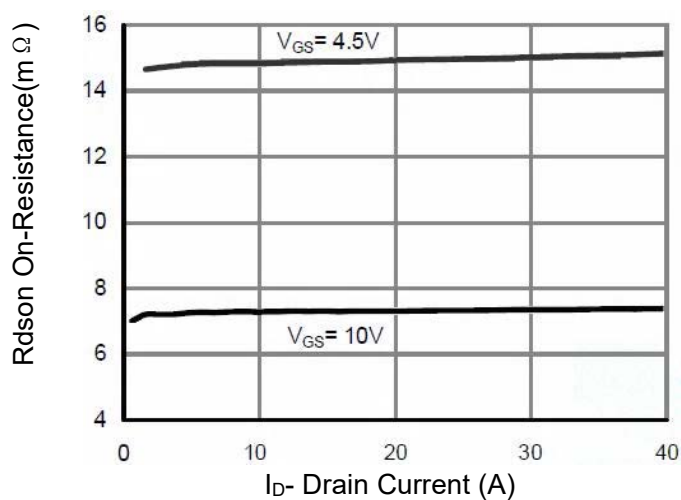


Figure 3 Rdson- Drain Current

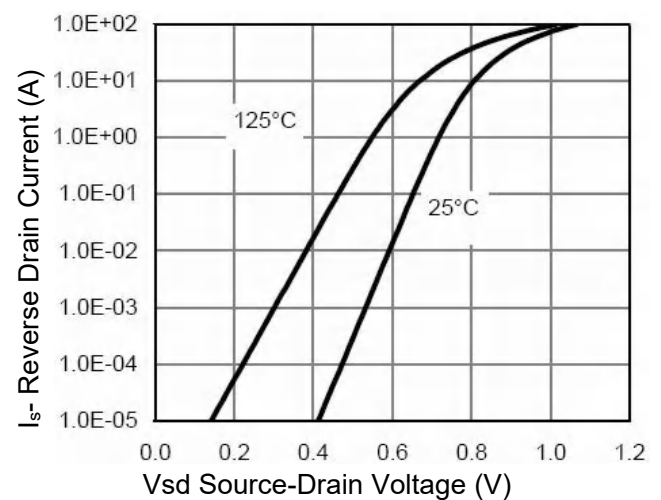


Figure 6 Source- Drain Diode Forward

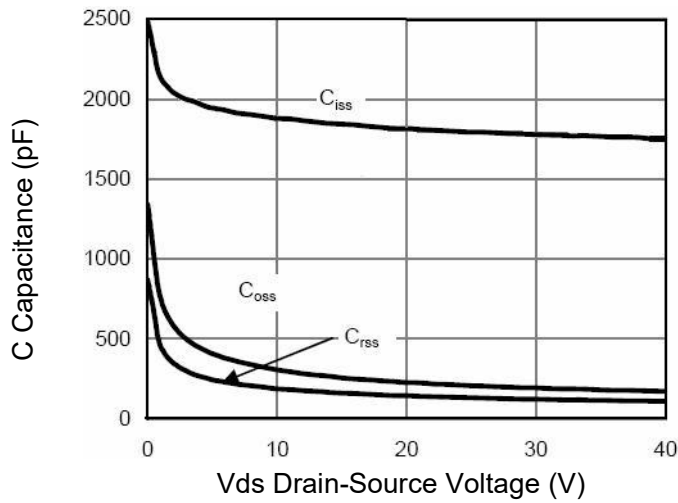


Figure 7 Capacitance vs Vds

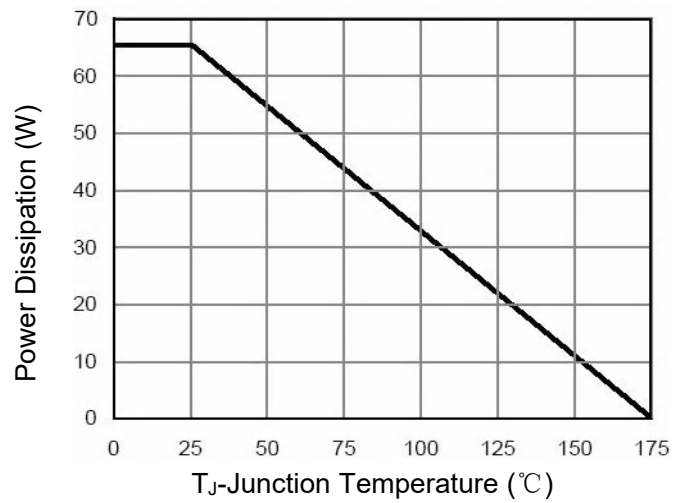


Figure 9 Power De-rating

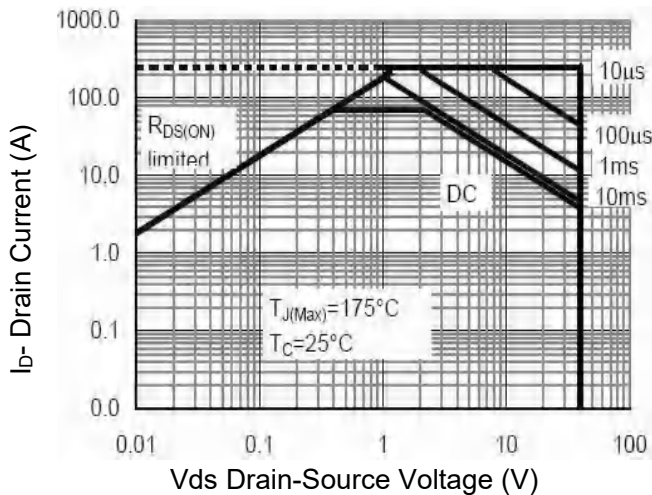


Figure 8 Safe Operation Area

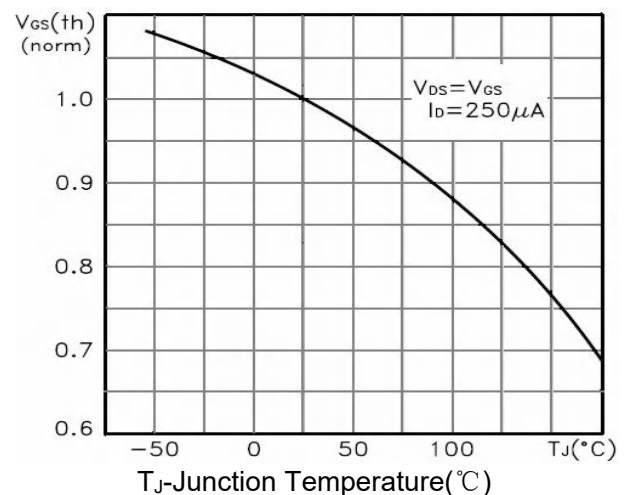


Figure 10  $V_{GS(th)}$  vs Junction Temperature

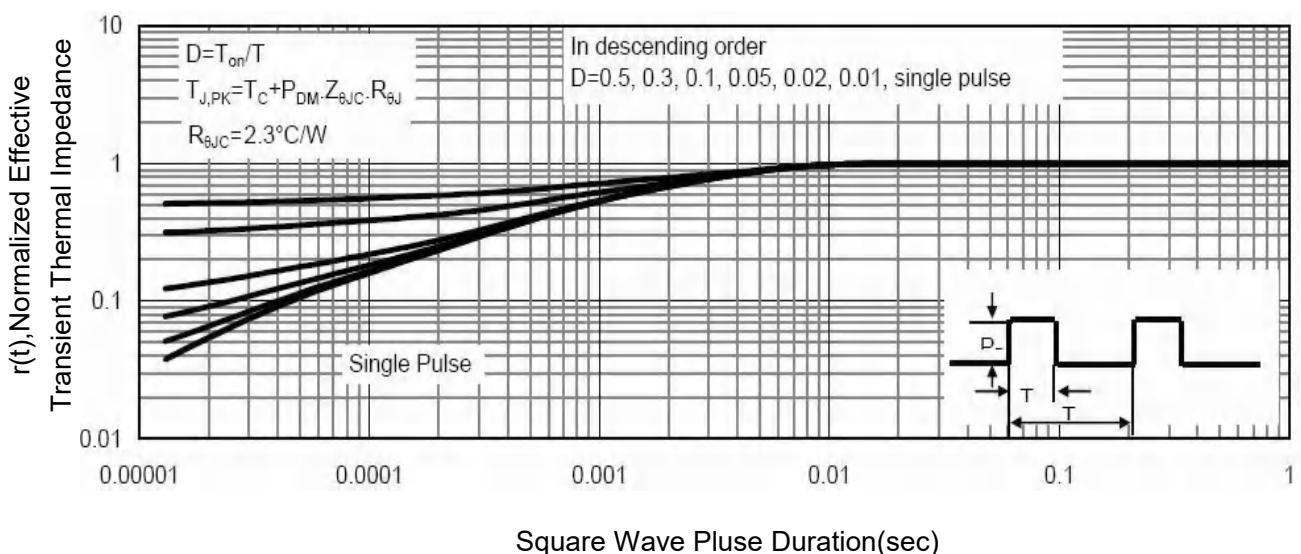
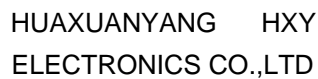


Figure 11 Normalized Maximum Transient Thermal Impedance



**FDD6635**  
N-Channel Enhancement Mode MOSFET

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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